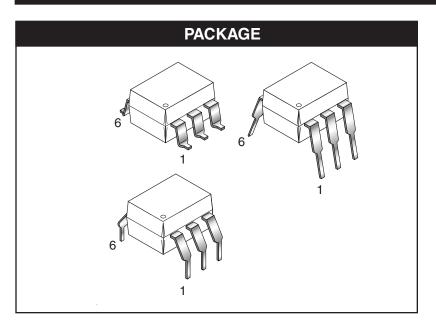
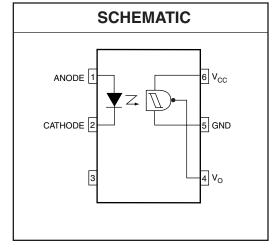


H11N1-M

H11N2-M

H11N3-M





DESCRIPTION

The H11NX-M series has a high speed integrated circuit detector optically coupled to an AlGaAs infrared emitting diode. The output incorporates a Schmitt trigger, which provides hysteresis for noise immunity and pulse s haping. The detector circuit is optimized for simplicity of operation and utilizes an open collector output for maximum application flexibility.

FEATURES

- High data rate, 5 MHz typical (NRZ)
- Free from latch up and oscilliation throughout voltage and temperature ranges.
- Microprocessor compatible drive
- Logic compatible output sinks 16 mA at 0.5 V maximum
- · Guaranteed on/off threshold hysteresis
- · Wide supply voltage capability, compatible with all popular logic systems
- High common mode transient immunity, 2000 V/µs minimum
- Fast switching $t_r = 7.5ns$ typical, $t_f = 12ns$ typical
- Underwriter Laboratory (UL) recognized—file #E90700
- VDE recognized File#102497 Add option V (e.g., H11N1VM)

APPLICATIONS

- Logic to logic isolator
- Programmable current level sensor
- Line receiver—eliminate noise and transient problems
- A.C. to TTL conversion—square wave shaping
- Interfaces computers with peripherals
- Isolated power MOS driver for power supplies

Truth Table

Input	Output
Н	L
L	Н

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H11N1-M

H11N2-M

H11N3-M

ABSOLUTE MAXIMUM RATINGS					
Parameters	Symbol	Device	Value	Units	
TOTAL DEVICE					
Storage Temperature	T _{STG}	All	-55 to +150	°C	
Operating Temperature	T _{OPR}	All	-40 to +85	°C	
Lead Solder Temperature	T _{SOL}	All	260 for 10 sec	°C	
Total Device Power Dissipation @ 25°C	PD	All	250	mW	
Derate Above 25°C	ГD	All	2.94	mW/°C	
EMITTER					
Continuous Forward Current	۱ _F	All	30	mA	
Reverse Voltage	V _R	All	6	V	
Forward Current - Peak (1 µs pulse, 300 pps)	I _F (pk)	All	1.0	А	
LED Power Dissipation 25°C Ambient	PD	P _D All		mW	
Derate Linearly From 25°C	ГD	All	1.41	mW/°C	
DETECTOR					
Detector Power Dissipation @ 25°C	Б	All	150	mW	
Derate Linearly from 25°C	PD	All	1.76	mW/°C	
V ₄₅ Allowed Range	V _O	All	0 to 16	V	
V ₆₅ Allowed Range	V _{CC}	All	0 to 16	V	
I ₄ Output Current	Ι _Ο	All	50	mA	

ELECTRICAL CHARACTERISTICS (T _A = 0-70°C Unless otherwise specified.) INDIVIDUAL COMPONENT CHARACTERISTICS									
						Parameters	Test Conditions	Symbol	Device
EMITTER									
In suit Fernievel Velterse	I _F = 10 mA	V _F	V	V	A 11		1.4	2	
Input Forward Voltage	I _F = 0.3 mA		All	0.75	1.25		V		
Reverse Current	V _R = 5 V	I _R	All			10	μA		
Capacitance	V = 0, f = 1.0 MHz	CJ	All			100	pF		
DETECTOR									
Operating Voltage Range		V _{CC}	All	4		15	V		
Supply Current	I _F = 0, V _{CC} = 5V	I _{CC(off)}	All		6	10	mA		
Output Current, High	$I_{\rm F} = 0.3 {\rm mA}, V_{\rm CC} = V_{\rm O} = 15 {\rm V}$	I _{ОН}	All			100	μA		

*Typical values at $T_A = 25^{\circ}C$

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H11N1-M

H11N2-M

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TRANSFER CHARACTERISTICS							
DC Characteristics	Test Conditions	Symbol	Device	Min	Тур*	Max	Units
Supply Current	I _F = 10mA, V _{CC} = 5V	I _{CC(on)}	All		6.5	10	mA
Output Voltage, low	$R_L=270\Omega, V_{CC}=5V, I_F=I_{F(on)} max.$	V _{OL}	All			0.5	V
	R _L =270Ω, V _{CC} = 5V note 1		H11N1-M	0.8		3.2	
Turn-On Threshold Current		I _{F(on)}	H11N2-M	2.3		5	mA
			H11N3-M	4.1		10	
Turn-Off Threshold Current	$R_L=270\Omega, V_{CC}=5V$	I _{F(off)}	All	0.3			mA
Hysteresis Ratio	$R_L=270\Omega, V_{CC}=5V$	I _{F(off)} /I _{F(on)}	All	0.65		0.95	
AC Characteristics	Test Conditions	Symbol	Device	Min	Тур	Max	Units
SWITCHING SPEED							
Propagation delay time High to Low	C=120pF, t _P =1µs, R _E : Note 2 Fig. 1	t _{PHL}	All		100	330	ns
Rise Time	C=120pF, t _P =1µs, R _E : Note 2 Fig. 1	t _r	All		7.5		ns
Propagation delay time Low to High	C=120pF, t _P =1µs, R _E : Note 2 Fig. 1	t _{PLH}	All		150	330	ns
Fall time	C=120pF, t _P =1µs, R _E : Note 2 Fig. 1	t _f	All		12		ns
Data Rate			All		5		MHz

ISOLATION CHARACTERISTICS						
Parameters	Test Conditions	Symbol	Min	Тур*	Max	Units
Input-Output Isolation Voltage	f = 60 Hz, t =1 sec.	V _{ISO}	7500			V _{PEAK}
Isolation Capacitance	V _{I-O} = 0V, f = 1 MHz	C _{ISO}		0.4	0.6	pF
Isolation Resistance	$V_{I-O} = \pm 500 \text{ VDC}$	R _{ISO}	10 ¹¹			Ω

*Typical values at $T_A = 25^{\circ}C$

NOTES:

1. Maximum I_{F(ON)} is the maximum current required to trigger the output. For example, a 3.2mA maximum trigger current would require the LED to be driven at a current greater than 3.2mA to guarantee the device will turn on. A 10% guard band is recommended to account for degradation of the LED over its lifetime. The maximum allowable LED drive current is 30mA.

2. H11N1: R_E = 910Ω H11N2: R_E = 560Ω

H11N3: R_E = 240Ω



H11N1-M

H11N2-M

H11N3-M

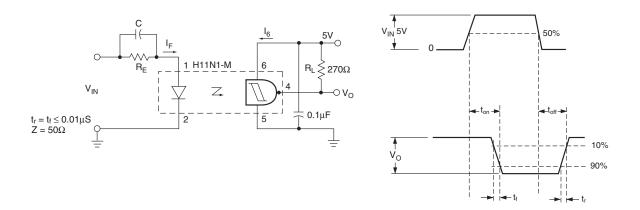
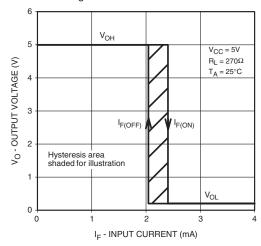
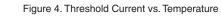
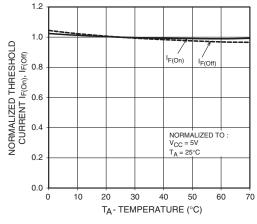


Figure 1. Switching Test Circuit and Waveforms

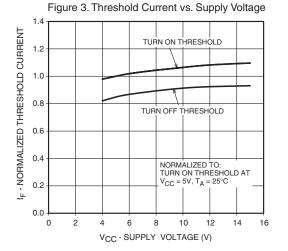
Figure 2. Transfer Characteristics



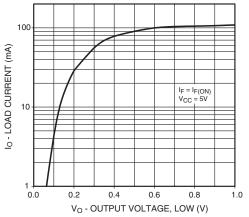




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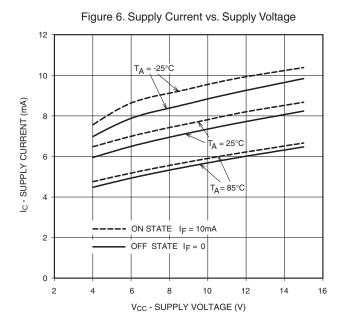




H11N1-M

H11N2-M

H11N3-M



 $100 \\ (U) \\ (U)$

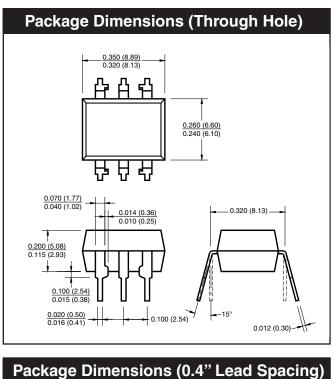
Figure 7. LED Forward Voltage vs. Forward Current



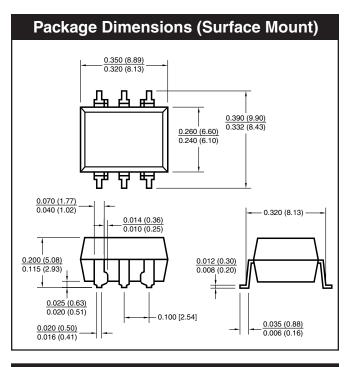
H11N1-M

H11N2-M

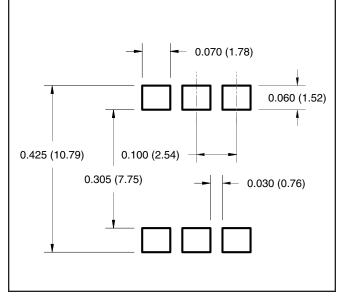
H11N3-M



$\begin{array}{c} & \begin{array}{c} 0.350 \ (6.89) \\ \hline 0.320 \ (6.13) \\ \hline 0.220 \ (6.10) \\ \hline 0.240 \ (6.10) \\ \hline 0.240 \ (6.10) \\ \hline 0.040 \ (1.02) \\ \hline 0.010 \ (0.25) \\ \hline 0.010 \ (0.25) \\ \hline 0.015 \ (0.38) \\ \hline 0.015 \ (0.39) \\ \hline 0.015 \ (0.39) \\ \hline 0.016 \ (0.41) \\ \hline \end{array}$



Recommended Pad Layout for Surface Mount Leadform





H11N1-M

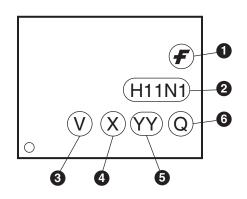
H11N2-M

H11N3-M

ORDERING INFORMATION

Option/Order Entry Identifier	Description
S	Surface Mount Lead Bend
SR2	Surface Mount; Tape and reel
Т	0.4" Lead Spacing
V	VDE 0884
TV	VDE 0884, 0.4" Lead Spacing
SV	VDE 0884, Surface Mount
SR2V	VDE 0884, Surface Mount, Tape & Reel

MARKING INFORMATION



Definitions				
1	Fairchild logo			
2	Device number			
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)			
4	One digit year code, e.g., '3'			
5	Two digit work week ranging from '01' to '53'			
6	Assembly package code			

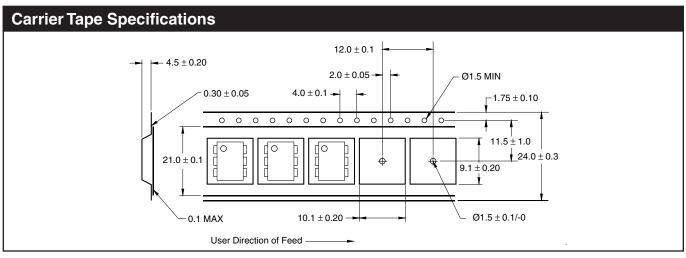
*Note – Parts that do not have the 'V' option (see definition 3 above) that are marked with date code '325' or earlier are marked in portrait format.



H11N1-M

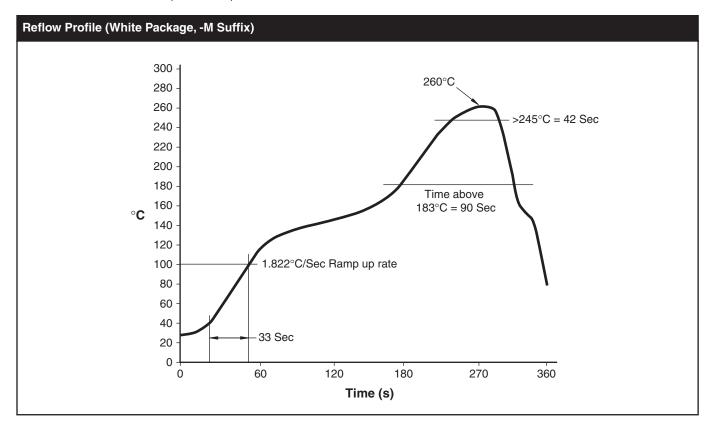
H11N2-M

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NOTE

All dimensions are in inches (millimeters)





SEMICONDUCTOR®

6-PIN DIP HIGH SPEED LOGIC OPTOCOUPLERS

H11N1-M

H11N2-M

H11N3-M

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